

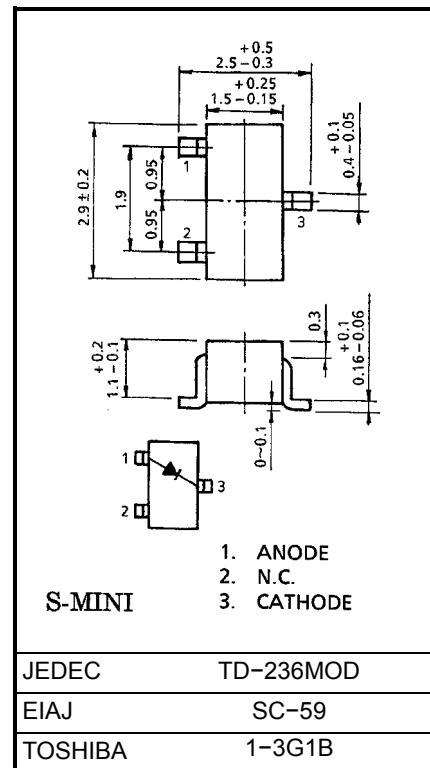
TOSHIBA Diode Silicon Epitaxial Schottky Planar Type

1SS349

Ultra High Speed Switching Application

- Low forward voltage : VF(3) = 0.49V (typ.)
- Low reverse current : IR = 50µA (max)
- Small package : SC-59

Unit: mm



Weight: 0.012g

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V _F (1)	—	I _F = 100mA	—	0.34	—	V
	V _F (2)	—	I _F = 500mA	—	0.42	—	
	V _F (3)	—	I _F = 1000mA	—	0.49	0.55	
Reverse current	I _R (1)	—	V _R = 20V	—	—	50	µA
Total capacitance	C _T	—	V _R = 0, f = 1MHz	—	250	—	pF

Marking

